

Formularium

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Basics

Symbols

- Absolute temperature: T
- Boltzmann constant: $k = 1.38064852 \times 10^{-23} \text{ m}^2 \text{ kg s}^{-2} \text{ K}^{-1}$
- Intrinsic free carrier concentration: n_i
- Electron concentration: n
- Hole concentration: p
- Effective density of states in conduction band: N_c
- Effective density of states in valence band: N_v
- Fermi level: ϕ_f
- Fermi energy: E_f
- Quasi Fermi energy for electrons (no equilibrium): E_{fn}
- Quasi Fermi energy for holes (no equilibrium): E_{fp}
- Intrinsic Fermi energy: E_i
- Valence band energy: E_v
- Conduction band energy: E_c
- Donor ionization energy: E_D
- Acceptor ionization energy: E_A
- Band gap energy: $E_g \triangleq E_c - E_v$
- Number of ionized donor ions: N_D
- Number of ionized acceptor ions: N_A
- Number of equivalent energy minima in conduction band: M_c
- Density-of-state effective electron mass: m_{de}
- Density-of-state effective hole mass: m_{dh}
- Recombination: R
- Thermal generation: G_{th}
- External generation: G
- Net recombination rate of electrons and holes: $U \triangleq R - G_{th}$
- Equilibrium electron concentration: n_{po}
- Equilibrium hole concentration: p_{no}
- Absorption coefficient: α
- Planck's constant: $6.62607015 \times 10^{-34} \text{ J s}$
- Photon frequency: ν
- ????: γ
- Auger recombination rate: R_A
- Auger coefficients: G_{An}, G_{Ap}
- Impact ionization generation rate: G_i
- Electron/hole ionization rate: α_n, α_p
- Free electron/hole velocity: v_n, v_p
- Impact ionization threshold energy: $E_{i,n}, E_{i,p}$
- Minority carrier effective lifetimes: τ_n, τ_p
- Electric field: ϵ
- Electrostatic potential: Ψ
- Thermal voltage: $V_t = kT/q$
- Electron/hole mobility: μ_n, μ_p
- Drift current density: J_{drift}
- Diffusion current density: $J_{\text{Diffusion}}$
- Diffusion constants: D_n, D_p

Concentration

$$n = N_c \exp\left(\frac{E_f - E_c}{kT}\right)$$

$$p = N_v \exp\left(\frac{E_v - E_f}{kT}\right)$$

$$N_c = 2 \left(\frac{2\pi m_{de} kT}{h^2} \right)^{3/2} M_c$$

$$N_v = 2 \left(\frac{2\pi m_{dh} kT}{h^2} \right)^{3/2}$$

Pure Semiconductor in Equilibrium

$$\begin{aligned}n &= p = n_i \\n_i^2 &= np = N_c N_v \exp\left(\frac{-E_g}{kT}\right) \\E_f &= E_i = \frac{E_c + E_v}{2} + \frac{kT}{2} \ln\left(\frac{N_v}{N_c}\right)\end{aligned}$$

Doped Semiconductor in Equilibrium

Charge neutrality:

$$N_D + p = N_A + n$$

N-type

$$\begin{aligned}N_D &> N_A \\n &= \frac{1}{2} \left(N_D - N_A + \sqrt{(N_D - N_A)^2 + 4n_i^2} \right) \\&\approx N_D - N_A \\p &= \frac{n_i^2}{n} \\&\approx \frac{n_i^2}{N_D - N_A} \\E_f &\approx E_i + kT \ln\left(\frac{N_D - N_A}{n_i}\right) > E_i\end{aligned}$$

P-type

$$\begin{aligned}N_A &> N_D \\p &= \frac{1}{2} \left(N_A - N_D + \sqrt{(N_A - N_D)^2 + 4n_i^2} \right) \\&\approx N_A - N_D \\n &= \frac{n_i^2}{p} \\&\approx \frac{n_i^2}{N_A - N_D} \\E_f &\approx E_i - kT \ln\left(\frac{N_A - N_D}{n_i}\right) < E_i\end{aligned}$$

Semiconductor out of Equilibrium

$$\begin{aligned}pn &> n_i^2 \\n &= N_c \exp\left(\frac{E_{fn} - E_c}{kT}\right) \\&= n_i \exp\left(\frac{E_{fn} - E_i}{kT}\right) \\p &= N_v \exp\left(\frac{E_v - E_{fp}}{kT}\right) \\&= n_i \exp\left(\frac{E_i - E_{fp}}{kT}\right) \\np &= N_c N_v \exp\left(\frac{(E_v - E_c) + (E_{fn} - E_{fp})}{kT}\right) \\&= n_i^2 \exp\left(\frac{E_{fn} - E_{fp}}{kT}\right)\end{aligned}$$

Carrier Recombination and Generation Mechanisms

$$\begin{aligned}U_n &\approx \frac{n - n_{po}}{\tau_n} \\U_p &\approx \frac{p - p_{no}}{\tau_p} \\\frac{dn}{dt} &= \frac{dp}{dt} = -U + G = G_{th} + G - R\end{aligned}$$

Shockley-Read-Hall generation and recombination

Impurities with energy levels within the forbidden gap.

U_{SRH} = staat hopelijk in het formularium

Radiative generation and recombination

Usually negligible for indirect semiconductors

$$R_r = Bnp$$

N-type

$$R_r = Bpn_0 = \frac{p}{\tau_p}$$

$$\tau_p = \frac{1}{Bn_0} \approx \frac{1}{BN_D}$$

$$U_r = \frac{p - p_0}{\tau_p}$$

P-type

$$R_r = Bnp_0 = \frac{n}{\tau_n}$$

$$\tau_n = \frac{1}{Bp_0} \approx \frac{1}{BN_A}$$

$$U_r = \frac{n - n_0}{\tau_n}$$

Radiative generation

$$\alpha = (h\nu - E_g)^\gamma \quad (h\nu > E_g)$$

Auger recombination and Impact Ionization

Auger recombination: Energy released by band-to-band recombination is given to another free hole or electron

$$R_A = G_{An}n^2p + G_{Ap}p^2n$$

$$R_A \approx G_{An}N_D^2p = \frac{p}{\tau_p} \quad \text{n-type}$$

$$R_A \approx G_{Ap}N_A^2n = \frac{n}{\tau_n} \quad \text{p-type}$$

Impact ionization: Kinetic energy of an electron or hole is released in a collision to a neutral atom and generates an electron-hole pair

$$G_i = \alpha_n n v_n + \alpha_p p v_p$$

$$\alpha_n(\varepsilon) = \frac{q\varepsilon}{E_{i,n}} \exp\left(-\frac{b}{\varepsilon}\right)$$

$$\alpha_p(\varepsilon) = \frac{q\varepsilon}{E_{i,p}} \exp\left(-\frac{b}{\varepsilon}\right)$$

Effective minority carrier lifetime

$$\frac{1}{\tau} = \frac{1}{\tau_{SRH}} + \frac{1}{\tau_{rad}} + \frac{1}{\tau_{Auger}}$$

Carrier Transport

$$\varepsilon = \frac{1}{q} \nabla E_i$$

$$\varepsilon = -\nabla \Psi$$

$$\Psi = -\frac{E_i}{q}$$

$$\phi_f = -\frac{E_f}{q}$$

Equilibrium:

$$n = n_i \exp\left(\frac{\Psi - \phi_f}{V_t}\right)$$

$$p = n_i \exp\left(\frac{\phi_f - \Psi}{V_t}\right)$$

Out of equilibrium:

$$n = n_i \exp\left(\frac{\Psi - \phi_{fn}}{V_t}\right)$$

$$p = n_i \exp\left(\frac{\phi_{fp} - \Psi}{V_t}\right)$$

$$pn = n_i^2 \exp\left(\frac{\phi_{fp} - \phi_{fn}}{V_t}\right)$$

Drift

$$v_n = -\mu_n \varepsilon$$

$$v_p = -\mu_p \varepsilon$$

TODO: p. II-24 - II-26

$$J_{\text{drift},n} = q\mu_n n \varepsilon = \sigma_n \varepsilon$$

$$J_{\text{drift},p} = q\mu_p p \varepsilon = \sigma_p \varepsilon$$

Diffusion

$$J_{\text{diffusion},n} = -qD_n (-\nabla n)$$

$$J_{\text{diffusion},p} = qD_p (-\nabla p)$$

$$D_n = \mu_n \frac{kT}{q}$$

$$D_p = \mu_p \frac{kT}{q}$$

Current equations

$$J_n = q\mu_n \left(n\varepsilon + \frac{kT}{q} \nabla n \right) = -q\mu_n n \nabla \phi_{fn}$$

$$J_p = q\mu_p \left(p\varepsilon - \frac{kT}{q} \nabla p \right) = -q\mu_p p \nabla \phi_{fp}$$

PN-junction

Symbols

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MOS-cap

MOSFET

N-FET

Fermi level

$$\phi_f = V_t \ln\left(\frac{N_A}{n_i}\right)$$

Threshold voltage

$$V_T = V_{FB} + 2\phi_f + \frac{\sqrt{2q\epsilon_s N_A}}{C_{ox}} \sqrt{2\phi_f - V_{BS}}$$

Drain-Source current:

$$I_{DS,\text{lin}} = \frac{\mu C_{ox} W}{L} \left(V_{GS} - V_T + \frac{V_{DS}}{2} \right) V_{DS}$$

$$I_{DS,\text{sat}} = \frac{\mu C_{ox} W}{2L} (V_{GS} - V_T)^2$$

BJT

PV cell

$$V_{oc} = V_t \ln\left(\frac{J_{sc}}{J_0}\right)$$

$$J_0 = q \sqrt{\frac{V_t \mu_p}{\tau_p}} \frac{n_i^2}{N_D}$$

$$I_{np} = I_{sc} - I_S \left[\exp\left(\frac{V_{pn}}{V_t}\right) - 1 \right]$$
